

## RTX3520S

The RTX3520S is a radiation tolerant TCXO in 35 x 20 mm hermetically sealed package. This TCXO is specifically designed for missions where resistance to demanding environment, short lead-time and radiation tolerance are required. The high reliability TCXO delivers excellent frequency stability.

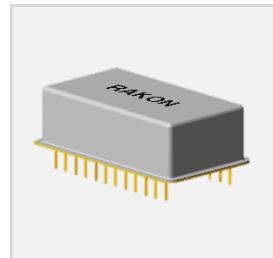
### Features

- TID limit of 100 kRad and latch-up free till 32.4/62 MeV
- Hermetically sealed package
- Frequency range: 5.5 to 375 MHz
- Output option: HCMOS and Sinewave
- Low current: 25 mA
- Supply voltage 5.0 or 15.0 V
- Excellent frequency stability:  $\pm 1$  ppm over -15 to 60°C
- Manufactured in accordance with: MIL-PRF-55310 Class 2, level S

### Applications

- Space Synthesizers and Transponders
- GPS receivers
- Down and up converters and on-board calculators
- FGU

35 x 20 mm



### Environmental Conditions

Parameter	Condition / Remarks	Min.	Typ.	Max.	Unit
Operating temperature		-15 -30		60 60	°C
Switch-on temperature	TS <sub>0</sub>	-40		65	°C
Non-operating temperature	TNOp	-55		125	°C

### Frequency Characteristics

Parameter	Condition / Remarks	Min.	Typ.	Max.	Unit
Initial frequency accuracy	@ 25°C			$\pm 0.3$	ppm
Frequency stability over temperature (FvT)	-15 to 60°C -30 to 60°C			$\pm 1$ $\pm 2$	ppm
Supply voltage stability (FvT) <sup>1</sup>				$\pm 0.2$	ppm
Ageing	Per year			$\pm 1$	ppm

### Electrical Interface

Parameter	Condition / Remarks	Min.	Typ.	Max.	Unit
Power supply (Vcc)	$\pm 5\%$ tolerance		5.0, 15.0		V
Input current <sup>1</sup>	No load		25		mA

### Frequency Adjustment Option

Parameter	Condition / Remarks	Min.	Typ.	Max.	Unit
Frequency adjustment range		$\pm 3$			ppm
Provision of frequency adjustment	By external resistor	0	5	10	kΩ

### Phase Noise

Parameter	5.5 to 155 MHz (Typ.)	156 to 250 MHz (Typ.)	251 to 375 MHz (Typ.)	Unit	
Offset	10 Hz 100 Hz 1 kHz 10 kHz	-75 -110 -130 -145	-67 -102 -122 -137	-64 -99 -119 -134	dBc/Hz

<sup>1</sup> Over temperature range

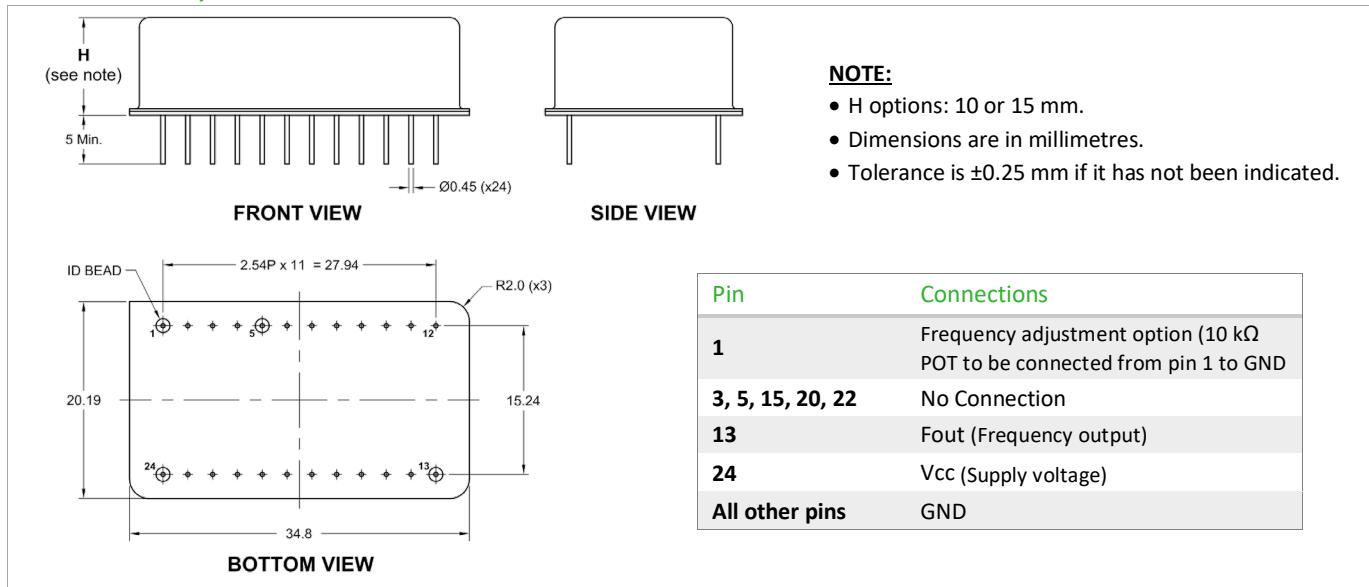
## Output Characteristics<sup>2</sup>

Parameter	Condition / Remarks	Min.	Typ.	Max.	Unit
HCMOS <sup>3</sup>	Nominal frequency	HCMOS output	5.5	50	MHz
	Output voltage (V <sub>OL</sub> ) <sup>1</sup>	15 pF load		10% V <sub>CC</sub>	V
	Output voltage (V <sub>OH</sub> ) <sup>1</sup>	15 pF load	90% V <sub>CC</sub>		V
	Duty cycle <sup>1</sup>	@50% V <sub>CC</sub>	45	55	%
	Rise time / fall time <sup>1</sup>	10% to 90% V <sub>CC</sub>		5	ns
Sinewave	Nominal frequency	Sinewave output	5.5	375	MHz
	Output level <sup>1</sup>	50 Ω nominal load	7		dBm
	Harmonics & subharmonics <sup>1</sup>			-45	dBc
	Spurious <sup>1</sup>			-70	dBc

## Screening (100%)

Screening Operation	Requirements and Condition
Non-destructive bond pull	MIL-STD-883, method 2023
Internal visual	MIL-STD-883, method 2017 and method 2032
Stabilization bake (prior to seal)	MIL-STD-883, method 1008, condition C (+150°C), 48 hours minimum
Thermal shock	MIL-STD-883, method 1011, condition A
Temperature cycling	MIL-STD-883, method 1010, condition C
Constant acceleration	MIL-STD-883, method 2001, condition A, Y1 only (5000 g's)
Seal (fine and gross leak)	MIL-STD-883, method 1014: <b>Fine leak</b> <i>Test condition A1, A2, or B</i> <b>Gross leak</b> <i>Test condition B2 or B3</i>
Particle impact noise detection (PIND)	MIL-STD-883, method 2020, condition A
Electrical test	Nominal and extreme supply voltages, specified load, 23°C and temperature extremes, record all test parameters by serial number
Burn-in (load)	125°C, nominal supply voltage and burn-in load, 240 hours minimum
Radiographic	MIL-STD-883, method 2012
External Visual	MIL-STD-883, method 2009

## Model Outline, Pin Connections


<sup>2</sup> LVDS option is available on request

<sup>3</sup> The HCMOS output is available for 5.0 V supply